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Attorney Docket Number

40004551-0025-002

	Application Number		10791334		
INFORMATION DISCLOSURE	Filing Date		2004-03-01		
	First Named Inventor	Gi Yo	oul Kim		
STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Art Unit		1792		
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	1	4389973		1983-06-28	Suntola, T.S. et al.			
	2	5281274		1994-01-25	Yoder, Max N.			
	3	5855675		1997-03-03	Doering, Kenneth et al.			
	4	5879459		1999-03-09	Gadgil, Prasad N. et al.			
	5	6042652		2000-03-28	Hyun, Kwang-soo et al.			
	6	6174377		2001-01-16	Doering, Kenneth et al.			
	7	6387185		2002-05-14	Doering, Kenneth et al.			
	8	6503330		2003-01-07	Sneh, Ofer et al.			

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		-					1						
	9	6270572			2001-08-07		Kim, Yeong-kwan et al.						
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	1	S.M. GEORGE "Atomic Layer Deposition: An Overview", Chem. Rev., 110, pp. 111-131 (2010)											
	2	R.A. WIND and S.M. GEORGE "Quartz Crystal Microbalance Studies of Al2O3 Atomic Layer Deposition Using Trimethylaluminum and Water at 125°C", J. Phys. Chem. A, 114, pp. 1281-1289 (2010)											

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				<u> </u>					
	1								
	3	J.W. ELAM et al., "Viscous Flow Reactor with Quartz Crystal Microbalance for Thin Film Growth by Atomic Layer Deposition", Rev. Sci. Instrum., 73, pp. 2981-2987 (2002)							
	4	A.W. OTT et al., "Al2O3 Thin Film Growth on Si(100) Using Binary Reaction Sequence Chemistry", Thin Solid Films, 292, pp. 135-144 (1997)							
	5	M.D. G	RONER et al., "Low Temp	perature Al2O3 Atomic Layer	Depos	ition", Chem. Mater., 16, p	pp. 639-645 (2004)		
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